High Power LED Series Chip on Board

LC008B



High efficacy COB LED package, well-suited for use in spotlight applications

Features & Benefits

- Chip on Board (COB) solution makes it easy to design in
- Simple assembly reduces manufacturing cost
- Low thermal resistance
- InGaN/GaN MQW LED with long time reliability
- Completed 6,000 hours of LM-80 Testing
- ENEC certified: Integral LED Module

Applications

- Spotlight / Downlight
- LED Retrofit Bulbs
- Outdoor Illumination







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1. Characteristics

a) Absolute Maximum Rating

ltem	Symbol	Rating	Unit	Condition
Ambient / Operating Temperature	T _a	-40 ~ +105	°C	-
Storage Temperature	T _{stg}	-40 ~ +120	°C	-
LED Junction Temperature	Tj	140	°C	-
Case Temperature	Тс	105	°C	*Note
Forward Current	I _F	430	mA	-
Power Dissipation	PD	15.8	W	_
ESD (HBM)	-	±2	kV	-
ESD (MM)	-	±0.5	kV	-

b) Electro-optical Characteristics ($I_F = 240 \text{ mA}, T_a = 25 \text{ °C}$)

ltem	Unit	Rank	Min.	Тур.	Max.
Forward Voltage (VF)	V	ΥH	33.5	36.5	39.5
		3	70	-	-
Opton Decide time Index (D.)		5	80	-	-
Color Rendering Index (Ra)	-	7	90	-	-
		8	95		
Thermal Resistance (junction to chip point)	°C/W		-	2.0	-
Beam Angle	o		_	115	_
Working Voltage for Insulation	V				50
Nominal Power	W			8.8	
Eye Protection		Risk 1	_		-

Notes:

- 1) The COB is tested in pulsed condition at rated test current (10 ms pulse width) and rated temperature ($T_j = T_c = T_a = 25$ °C)
- 2) Samsung maintains measurement tolerance of: forward voltage = ± 5 %, CRI = ± 1
- 3) Max Tc=105℃ (at max current) is for ENEC condition. Refer to the derating curve, '3. Typical Characteristics Graph' designed within the range.



c) Luminous Flux Characteristics (IF = 240 mA, Ta = 25 °C)

CRI (R _a)	Nominal	Flux	Flux	Sorting ¹⁾ @ ⁻	T _c = 25 °C (Im)	Calculated Flux ²⁾	@ $T_c = 85 ^{\circ}C$ (In
Min.	CCT (K)	Rank	Bin	Min.	Max.	Min.	Max.
	3000	MC	M1	1064	1209	958	1088
	3000	MG	M2	1209	1354	1088	1219
70	4000	MG	M1	1117	1270	1006	1143
70	4000	IVIG	M2	1270	1422	1143	1280
	5000	MG	M1	1128	1282	1015	1154
	5000	IVIG	M2	1282	1436	1154	1292
			K2	968	1041	881	947
		KE	K3	1041	1114	947	1014
	2700		K4	1114	1187	1014	1080
		KG	K3	1041	1114	947	1014
		NG	K4	1114	1187	1014	1080
			K2	1030	1108	937	1008
		KE	K3	1108	1185	1008	1078
	3000		K4	1185	1263	1078	1149
		KC	K3	1108	1185	1008	1078
		KG	K4	1185	1263	1078	1149
			K2	1061	1141	965	1038
		KE	K3	1141	1221	1038	1111
	3500		K4	1221	1300	1111	1183
		KO	K3	1141	1221	1038	1111
80		KG	K4	1221	1300	1111	1183
80			K2	1092	1174	994	1068
		KE	K3	1174	1256	1068	1143
	4000		K4	1256	1338	1143	1218
		KO	K3	1174	1256	1068	1143
		KG	K4	1256	1338	1143	1218
			K2	1102	1185	1003	1078
		KE	K3	1185	1268	1078	1154
	5000		K4	1268	1351	1154	1229
		1/2	K3	1185	1268	1078	1154
		KG	K4	1268	1351	1154	1229
			K2	1102	1185	1003	1078
		KE	K3	1185	1268	1078	1154
	5700		K4	1268	1351	1154	1229
		140	K3	1185	1268	1078	1154
		KG	K4	1268	1351	1154	1229



c) Luminous Flux Characteristics (IF = 240 mA, Ta = 25 °C)

CRI (R _a)	Nominal	Flux	Flux	Sorting ¹⁾ @T	_c = 25 °C (lm)	Calculated Flux ²⁾	@ $T_c = 85 ^{\circ}C$ (lm)
Min.	CCT (K)	Rank	Bin	Min.	Max.	Min.	Max.
			F2	859	933	781	849
	2700	FG	F3	933	1008	849	917
			F4	1008	1083	917	985
			F2	876	952	797	867
	3000	FG	F3	952	1029	867	936
90			F4	1029	1105	936	1005
90			F2	903	981	821	893
	3500	FG	F3	981	1060	893	964
			F4	1060	1138	964	1036
			F2	929	1010	845	919
	4000	FG	F3	1010	1090	919	992
			F4	1090	1171	992	1066
	2700	FC	E1	756	840	688	764
	2700	EC	E2	840	924	764	841
05	2000	FC	E1	779	866	709	788
95	3000	EC	E2	866	953	788	867
	2500	FC	E1	803	892	731	812
	3500	EC	E2	892	981	812	893

Notes:

1) The COB is tested in pulsed condition at rated test current (10 ms pulse width) and rated temperature ($T_j = T_c = T_a = 25$ °C)

2) Calculated flux values are for reference only

3) Samsung maintains measurement tolerance of: luminous flux = ± 7 %, CRI = ± 1



2. Product Code Information

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
S																	

Digit	PKG Information	Code				Specificat	tion
1 2 3	Samsung Package High Power	SPH					
4 5	Color	ww	Warm White	(T/U/	V/W Rank	s)	
4 0	Color	CW	Cool White	(Q/R	Ranks)		
6	Product Version	1					
78	Form Factor	HD	СОВ				
9	Lens Type	N	No lens				
10	Internal Code	9	LC008				
11	Chip Type	4					
		3	Min. 70				
12	CRI & Sorting Temperature	5	Min. 80 25	°C			
12		7	Min. 90				
		8	Min 95				
13 14	Forward Voltage (V)	YH	33.5~39.5				
		W	2700 K		WA,WB	(MacAdam Ellipse)	
		v	3000 K		VA, VB	(MacAdam Ellipse)	VW, VX, VY, VZ (ANSI bin)
15	CCT (K)	U		Bin	UA, UB	(MacAdam Ellipse)	
15	001 (K)	т	4000 K ^{Co}	ode:	TA, TB	(MacAdam Ellipse)	TW, TX, TY, TZ (ANSI bin)
		R	5000 K		RA	(MacAdam Ellipse)	RW, RX, RY, RZ (ANSI bin)
		Q	5700 K				QW, QX, QY, QZ (ANSI bin)
		2	MacAdam 2-s	step			
16	MacAdam / ANSI	3	MacAdam 3-s	step			
		т	ANSI bin				
		MG			M1, M2	(70 CRI)	
		KE			K2, K3, K	4 (80 CRI)	
17 18	Luminous Flux	KG	E	Bin ode:	K3, K4 (80 CRI)	
		FG			F2, F3, F4	4 (90 CRI)	
		EC			E1, E2 (95	5 CRI)	



a) Binning Structure (IF = 240 mA, Ta = 25 °C)

CRI (R₄) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , Im)	
	3000	SPHWW1HDN943YHVTMG	ΥH	VT	VW, VX	MG	M1	1064 ~ 1209	
	3000	SPHWWINDIN943THVIIVIG	ГП	VI	VY, VZ	IVIG	M2	1209 ~ 1354	
70	4000	SPHWW1HDN943YHTTMG	ΥH	Π	TW, TX	MG	M1	1117 ~ 1270	
70	4000	3FHWWIHD109431H11WG		11	TY, TZ	IVIG	M2	1270 ~ 1422	
	5000	SPHCW1HDN943YHRTMG	ΥH	RT	RW, RX	MG	M1	1128 ~ 1282	
	5000	SPHOW HIDNS43THINING	111	111	RY, RZ	IVIG	M2	1282 ~ 1436	
							K2	968 ~ 1041	
		SPHWW1HDN945YHW2KE	ΥH	W2	WB	KE	K3	1041 ~ 1114	
							K4	1114 ~ 1187	
							K2	968 ~ 1041	
	2700	SPHWW1HDN945YHW3KE	YH	W3	WA, WB	KE	K3	1041 ~ 1114	
	2700						K4	1114 ~ 1187	
		SPHWW1HDN945YHW2KG	YH	W2	WB	KG	K3	1041 ~ 1114	
		3PHWW1HD109431HW2KG	ГП	VVZ	VVD	NG	K4	1114 ~ 1187	
		SPHWW1HDN945YHW3KG	ΥH	14/2		KC	K3	1041 ~ 1114	
		3PHWW1HDN9431HW3KG	ΤΠ	W3	WA, WB	KG	K4	1114 ~ 1187	
							K2	1030 ~ 1108	
		SPHWW1HDN945YHV2KE	ΥH	V2	VB	KE	K3	1108 ~ 1185	
							K4	1185 ~ 1263	
	0000	0000						K2	1030 ~ 1108
00			SPHWW1HDN945YHV3KE	ΥH	V3	VA, VB	KE	K3	1108 ~ 1185
80	3000						K4	1185 ~ 1263	
			N/LL			140	K3	1108 ~ 1185	
		SPHWW1HDN945YHV2KG	ΥH	V2	VB	KG	K4	1185 ~ 1263	
			N/LL	1/0		140	K3	1108 ~ 1185	
		SPHWW1HDN945YHV3KG	ΥH	V3	VA, VB	KG	K4	1185 ~ 1263	
							K2	1061 ~ 1141	
		SPHWW1HDN945YHU2KE	ΥH	U2	UB	KE	K3	1141 ~ 1221	
							K4	1221 ~ 1300	
							K2	1061 ~ 1141	
	3500	SPHWW1HDN945YHU3KE	ΥH	U3	UA, UB	KE	K3	1141 ~ 1221	
							K4	1221 ~ 1300	
						140	K3	1141 ~ 1221	
		SPHWW1HDN945YHU2KG	ΥH	U2	UB	KG	K4	1221 ~ 1300	
							K3	1141 ~ 1221	
		SPHWW1HDN945YHU3KG	ΥH	U3	UA, UB	KG	K4	1221 ~ 1300	



a) Binning Structure (IF = 240 mA, $T_a = 25 \text{ °C}$)

CRI (R₀) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , Im)							
							K2	1092 ~ 1174							
		SPHWW1HDN945YHT2KE	ΥH	T2	ТВ	KE	K3	1174 ~ 1256							
							K4	1256 ~ 1338							
							K2	1092 ~ 1174							
	4000	SPHWW1HDN945YHT3KE	ΥH	Т3	ΤΑ, ΤΒ	KE	K3	1174 ~ 1256							
	-000						K4	1256 ~ 1338							
		SPHWW1HDN945YHT2KG	ΥH	T2	ТВ	KG	K3	1174 ~ 1256							
		SFTIWWITIDN943TTTZKG			ID	NG	K4	1256 ~ 1338							
		SPHWW1HDN945YHT3KG	ΥH	Т3	TA, TB	KG	K3	1174 ~ 1256							
		or now mibro-or more		10	17,10	i Ku	K4	1256 ~ 1338							
							K2	1102 ~ 1185							
		SPHCW1HDN945YHR3KE	ΥH	R3	RA	KE	K3	1185 ~ 1268							
80							K4	1268 ~ 1351							
														K2	1102 ~ 1185
	5000	SPHCW1HDN945YHRTKE	ΥH	RT	RW, RX, RY, RZ	KE	K3	1185 ~ 1268							
							K4	1268 ~ 1351							
		SPHWW1HDN945YHR3KG	ΥH	R3	RA	KG	K3	1185 ~ 1268							
					101		K4	1268 ~ 1351							
		SPHWW1HDN945YHRTKG	ΥH	RT	RW, RX,	KG	K3	1185 ~ 1268							
					RY, RZ		K4	1268 ~ 1351							
							K2	1102 ~ 1185							
		SPHCW1HDN945YHQTKE	ΥH	QT	QW, QX, QY, QZ	KE	K3	1185 ~ 1268							
	5700						K4	1268 ~ 1351							
		SPHWW1HDN945YHQTKG	ΥH	QT	QW, QX,	KG	K3	1185 ~ 1268							
		S. HAW HIDNOTOTHQ INC		9	QY, QZ	NG	K4	1268 ~ 1351							

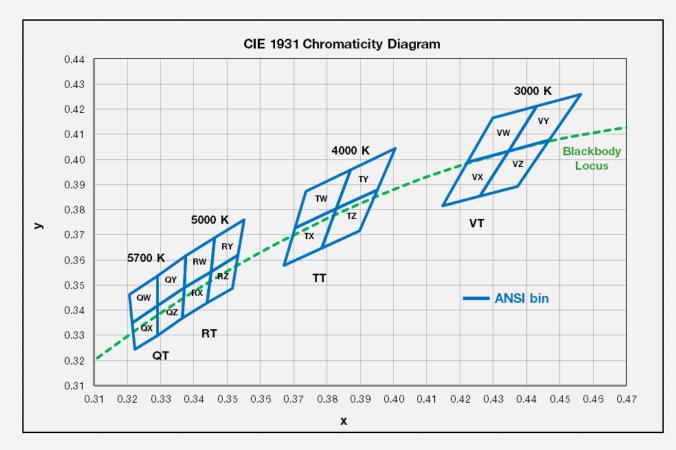


a) Binning Structure (I= 240 mA, $T_a = 25 \text{ °C}$)

CRI (R₂) Min.	Nominal CCT (K)	Product Code	V _F Rank	Color Rank	Chrom. Bin	Flux Rank	Flux Bin	Flux Range (Φ _v , Im)
							F2	859 ~ 933
		SPHWW1HDN947YHW2FG	ΥH	W2	WB	FG	F3	933 ~ 1008
	2700						F4	1008 ~ 1083
	2700						F2	859 ~ 933
		SPHWW1HDN947YHW3FG	ΥH	W3	WA, WB	FG	F3	933 ~ 1008
							F4	1008 ~ 1083
							F2	876 ~ 952
		SPHWW1HDN947YHV2FG	ΥH	V2	VB	FG	F3	952 ~ 1029
	2000						F4	1029 ~ 1105
	3000						F2	876 ~ 952
		SPHWW1HDN947YHV3FG	ΥH	V3	VA, VB	FG	F3	952 ~ 1029
00							F4	1029 ~ 1105
90							F2	903 ~ 981
		SPHWW1HDN947YHU2FG	ΥH	U2	UB	FG	F3	981 ~ 1060
	0500						F4	1060 ~ 1138
	3500						F2	903 ~ 981
		SPHWW1HDN947YHU3FG	ΥH	U3	UA, UB	FG	F3	981 ~ 1060
							F4	1060 ~ 1138
							F2	929 ~ 1010
		SPHWW1HDN947YHT2FG	ΥH	T2	ТВ	FG	F3	1010 ~ 1090
	4000						F4	1090 ~ 1171
	4000						F2	929 ~ 1010
		SPHWW1HDN947YHT3FG	ΥH	ТЗ	ΤΑ, ΤΒ	FG	F3	1010 ~ 1090
							F4	1090 ~ 1171
						=0	E1	756 ~ 840
		SPHWW1HDN948YHW2EC	ΥH	W2	WB	EC	E2	840 ~ 924
	2700						E1	756 ~ 840
		SPHWW1HDN948YHW3EC	ΥH	W3	WA,WB	EC	E2	840 ~ 924
							E1	779 ~ 866
		SPHWW1HDN948YHV2EC	ΥH	V2	VB	EC	E2	866 ~ 953
95	3000						E1	779 ~ 866
		SPHWW1HDN948YHV3EC	ΥH	V3	VA,VB	EC	E2	866 ~ 953
							E1	803 ~ 892
		SPHWW1HDN948YHU2EC	ΥH	U2	UB	EC	E2	892 ~ 981
	3500						E1	803 ~ 892
		SPHWW1HDN948YHU3EC	ΥH	U3	UA,UB	EC	E2	892 ~ 981





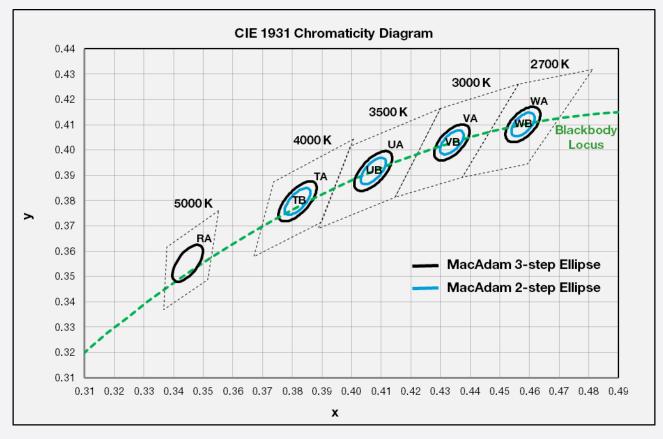


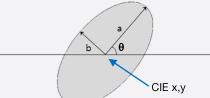
Region	CIE x	CIE y	Region	CIE x	CIE y
		V rank	(3000 K)		
	0.4223	0.399		0.4345	0.4033
104/	0.4345	0.4033	10/	0.4468	0.4077
VW	0.4431	0.4213	VY	0.4562	0.4260
	0.4299	0.4165		0.4431	0.4213
	0.4223	0.399		0.4260	0.3854
10/	0.4147	0.3814		0.4373	0.3893
VX	0.4260	0.3854	VZ	0.4468	0.4077
	0.4345	0.4033		0.4345	0.4033
		R rank	(5000 K)		
	0.3376	0.3616		0.3463	0.3687
DIA	0.3463	0.3687	DV.	0.3551	0.3760
RW	0.3451	0.3554	RY	0.3533	0.3620
	0.3371	0.3490		0.3451	0.3554
	0.3371	0.3490		0.3451	0.3554
DV	0.3451	0.3554	67	0.3533	0.3620
RX	0.3440	0.3428	RZ	0.3515	0.3487
	0.3366	0.3369		0.3440	0.3428

Region	CIE x	CIE y	Region	CIE x	CIE y
		T rank	(4000 K)		
	0.3736	0.3874		0.3871	0.3959
714/	0.3871	0.3959		0.4006	0.4044
TW	0.3828	0.3803	TY	0.3952	0.388
	0.3703	0.3726		0.3828	0.3803
	0.3703	0.3726		0.3828	0.3803
ТХ	0.3828	0.3803	77	0.3952	0.388
	0.3784	0.3647	ΤΖ	0.3898	0.3716
	0.367	0.3578		0.3784	0.3647
		Q rank	(5700 K)		
	0.3207	0.3462		0.3290	0.3538
014/	0.3290	0.3538	01	0.3376	0.3616
QW	0.3290	0.3417	QY	0.3371	0.3490
	0.3215	0.3350	4	0.3290	0.3417
	0.3215	0.3350		0.3290	0.3417
QX	0.3290	0.3417	QZ	0.3371	0.3490
QX	0.3290	0.3300	QZ	0.3366	0.3369
	0.3222	0.3243		0.3290	0.3300









MacAdam Ellipse (WA, WB)								
Step	Step CIE x CIE y θ a b							
2-step	0.4578	0.4101	53.70	0.0054	0.0028			
3-step	0.4578	0.4101	53.70	0.0081	0.0042			

MacAdam Ellipse (UA, UB)								
Step CIE x CIE y θ a b								
2-step	0.4073	0.3917	54.00	0.0062	0.0028			
3-step	0.4073	0.3917	54.00	0.0093	0.0041			

MacAdam Ellipse (RA)								
Step	CIE x	CIE y			b			
3-step	0.3447	0.3553	59.62	0.0082	0.0035			

MacAdam Ellipse (VA, VB)						
Step	CIE x	CIE y			b	
2-step	0.4338	0.403	53.22	0.0056	0.0027	
3-step	0.4338	0.4030	53.22	0.0083	0.0041	

MacAdam Ellipse (TA, TB)						
Step	CIE x	CIE y			b	
2-step	0.3818	0.3797	53.72	0.0063	0.0027	
3-step	0.3818	0.3797	53.72	0.0094	0.0040	

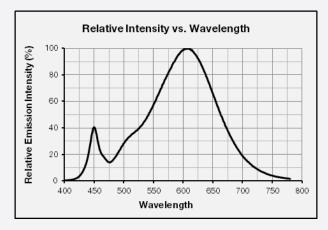
Note:

Samsung maintains measurement tolerance of: $Cx, Cy = \pm 0.005$



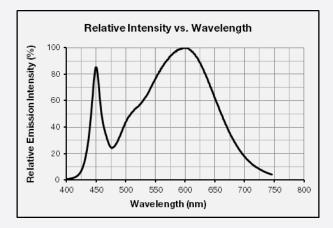
3. Typical Characteristics Graphs

a) Spectrum Distribution ($I_F = 240 \text{ mA}, T_a = 25 \text{ °C}$)

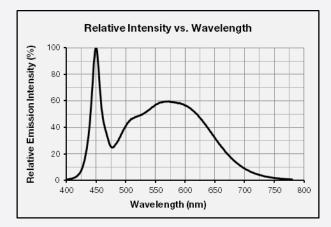


сст: 3500 к

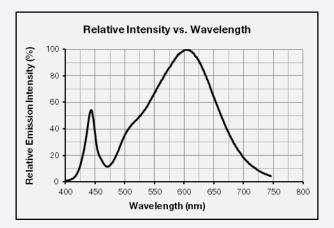
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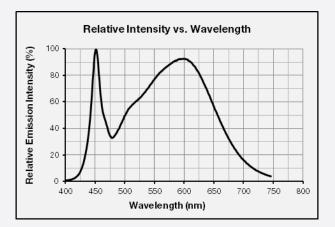




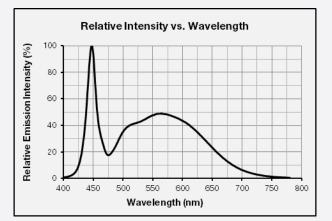
ССТ: 3000 К



ССТ: 4000 К

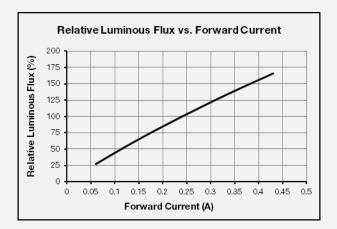


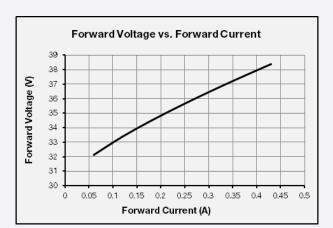




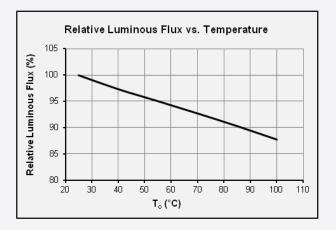


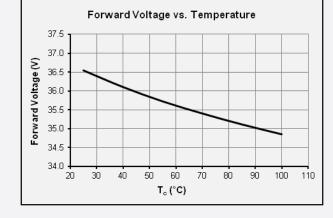






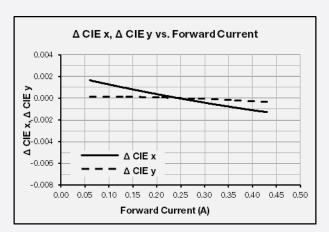
c) Temperature Characteristics ($I_F = 240 \text{ mA}$)



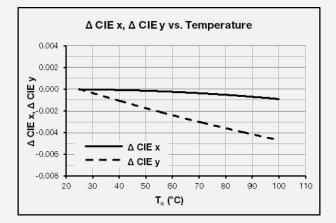


d) Color Shift Characteristics

T_a = 25 °C

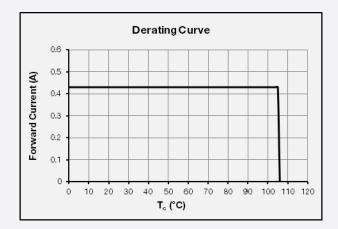


I_F = 240 mA

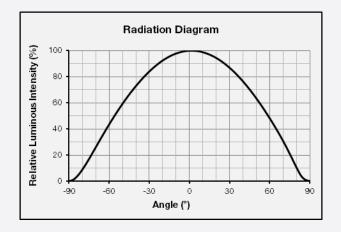




e) Derating Curve



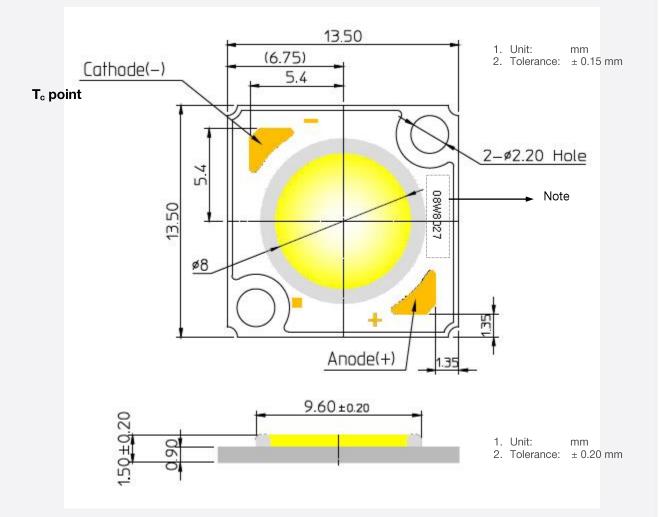
f) Beam Angle Characteristics (I_F = 240 mA, $T_a = 25$ °C)







4. Outline Drawing & Dimension



Item	Dimension	Tolerance	Unit
Length	13.50	±0.15	mm
Width	13.50	±0.15	mm
Height	1.50	±0.20	mm
Light Emitting Surface (LES) Diameter	8	±0.15	mm
Screw Hole Size	2.2	±0.15	mm

Note: Denoted product information above is only an example (08W8027:8.6W, CRI80+, 2700K)



5. Reliability Test Items & Conditions

a) Test Items

Test Item	Test Condition	Test Hour / Cycle
Room Temperature Life Test	25 °C, I _F = max	1000 h
High Temperature Humidity Life Test	60 °C, 90 % RH, DC Derating, I _F = max	1000 h
High Temperature Life Test	105 °C, DC Derating, I_F = max	1000 h
Low Temperature Life Test	-40 °C, DC 430 mA	1000 h
High Temperature Storage	120 °C	1000 h
Low Temperature Storage	-40 °C	1000 h
Thermal Shock	-45 °C / 15 min ↔ 125 °C / 15 min temperature change in 5 min	200 cycles
Temperature Cycle On/Off Test	-40 °C / 85 °C each 20 min, 100 min transfer power on/off each 5 min, DC 240 mA	100 cycles
ESD (HBM)	R ₁ : 10 MΩ R ₂ : 1.5 kΩ C: 100 pF V: ±2 kV	5 times
ESD (MM)	R ₁ : 10 MΩ R ₂ : 0 kΩ C: 200 pF V: ±0.5 kV	5 times
Vibration Test	20 ~ 80 Hz (displacement: 0.06 inch, max. 20 g) 80 ~ 2 kHz (max. 20 g) min. frequency ↔ max. frequency 4 min transfer	4 times
Mechanical Shock Test	1500 g, 0.5 ms each of the 6 surfaces (3 axis x 2 sides)	5 times
Salt Spray Test	35 °C, 5 % salt water 8 h spray, 16 h dwell	2 cycles

b) Criteria for Judging the Damage

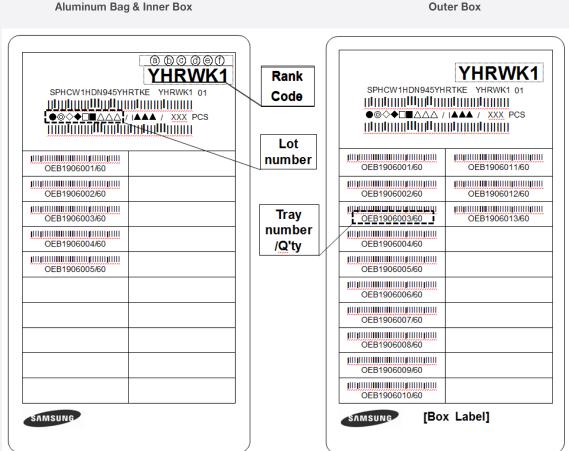
ltem	Symbol	Test Condition	Limit		
item	Symbol	(T _c = 25 °C)	Min.	Max.	
Forward Voltage	V _F	$I_F = 240 \text{ mA}$	L.S.L. * 0.9	U.S.L. * 1.1	
Luminous Flux	Φ _v	$I_F = 240 \text{ mA}$	L.S.L * 0.7	U.S.L * 1.3	



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6. Label Structure

a) Label Structure



Note: Denoted rank code and product code above is only an example (see description on page 5)

Rank Code:

- (a) b: Forward Voltage rank (refer to page 6-7)
- ©d: Chromaticity bin (refer to page 8-9)
- (e) f): Luminous Flux bin (refer to page 6-7)



Outer Box

b) Lot Number

The lot number is composed of the following characters:

$\bigcirc \bigcirc \diamondsuit \blacklozenge \square \blacksquare \triangle \triangle \triangle / 1 \blacktriangle \blacktriangle \land xxx PCS$

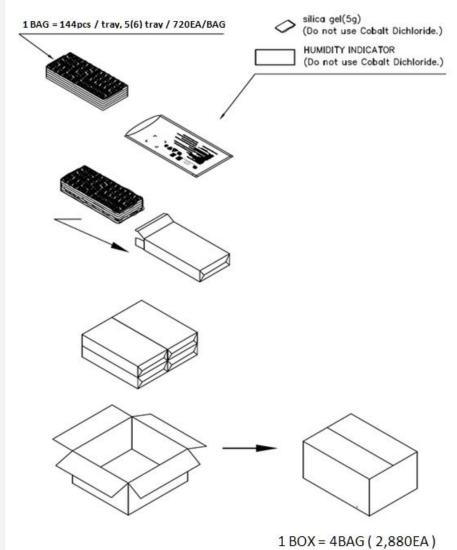
•	:	Production site (S: Giheung, Korea, G: Tianjin, China)
\bigcirc	:	L (LED)
\diamond	:	Product state (A: Normal, B: Bulk, C: First Production, R: Reproduction, S: Sample)
•	:	Year (Y: 2014, Z: 2015, A: 2016,)
	:	Month (1~9, A, B, C)
•	:	Day (1~9, A, B~V)
$\triangle \triangle \triangle$:	Product serial number (001 ~ 009)
	:	Tray number (001 ~ 999)



7. Packing Structure

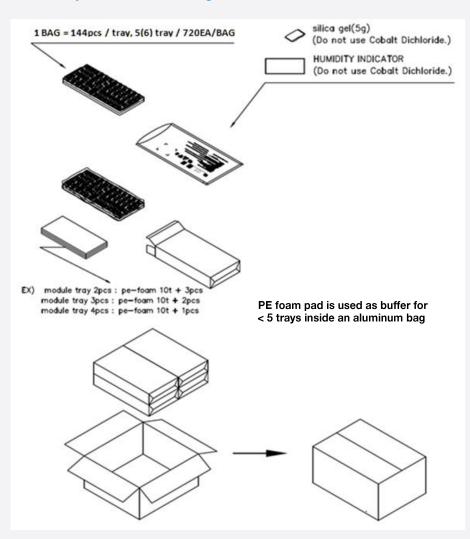
De alvia a restarial	Max. quantity		Dimension (mm)			
Packing material	in pcs of COB	Length	Width	Height	Tolerance	
Tray	144	322.6	135.9	11	0.25	
Aluminum Bag	720 (5 trays)	450	230	-	10	
PE Foam Pad	-	280	130	10	2	
Inner Box	720 (1 aluminum bag)	338	143	55	2	
Outer Box	2880 (4 inner boxes)	346	303	120	5	
Pallet	161,280 (56 outer boxes)	1000	1000	970	10	

a) Packing Structure for 5 trays inside Aluminum Bag

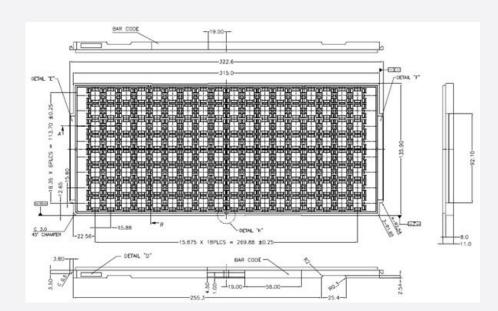




b) Packing Structure for <5 trays inside Aluminum Bag

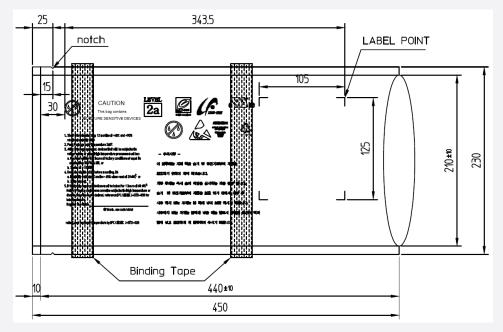


c) Tray





d) Aluminum Vinyl Packing Bag



e) Silica Gel & Humidity Indicator Card inside Aluminum Vinyl Packing Bag

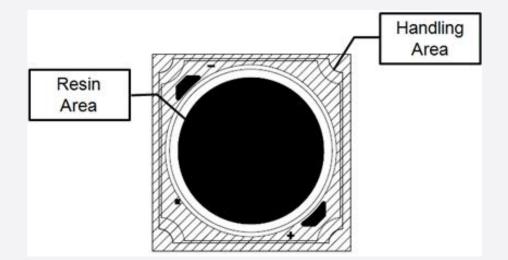






8. Precautions in Handling & Use

- This device should not be used in any type of fluid such as water, oil, organic solvent, etc. When cleaning is required, IPA is recommended as the cleaning agent. Some solvent-based cleaning agent may damage the silicone resins used in the device.
- 2) LEDs must be stored in a clean environment. If the LEDs are to be stored for three months or more after being shipped from Samsung, they should be packed with a nitrogen-filled container (shelf life of sealed bags is 12 months at temperature 0~40 °C, 0~90 % RH).
- After storage bag is opened, device subjected to soldering, solder reflow, or other high temperature processes must be:
 a. Mounted within 672 hours (28 days) at an assembly line with a condition of no more than 30 °C / 60 % RH, or
 b. Stored at <10 % RH
- 4) Repack unused products with anti-moisture packing, fold to close any opening and then store in a dry place.
- 5) Devices require baking before mounting, if humidity card reading is >60 % at 23 ± 5 °C.
- 6) Devices must be baked for 1 hour at 60 ± 5 °C, if baking is required.
- 7) The LEDs are sensitive to the static electricity and surge current. It is recommended to use a wrist band or antielectrostatic glove when handling the LEDs. If voltage exceeding the absolute maximum rating is applied to LEDs, it may cause damage or even destruction to LED devices. Damaged LEDs may show some unusual characteristics such as increase in leakage current, lowered turn-on voltage, or abnormal lighting of LEDs at low current.
- 8) VOCs (Volatile Organic Compounds) can be generated from adhesives, flux, hardener or organic additives used in luminaires (fixtures). Transparent LED silicone encapsulant is permeable to those chemicals and they may lead to a discoloration of encapsulant when they exposed to heat or light. This phenomenon can cause a significant loss of light emitted (output) from the luminaires. In order to prevent these problems, we recommend users to know the physical properties of materials used in luminaires and they must be carefully selected.
- 9) The resin area is very sensitive, please do not handle, press, touch, rub, clean, or pick by with tweezers on it. Instead, please pick at the handling area as indicated below.





Legal and additional information.

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